NSN 5962-01-372-9625

Memory Microcircuit - Page 1 of 2



View Online at https://aerobasegroup.com/nsn/5962-01-372-9625

1.2 watts

Operating Tempurature Range:

-55.0/+125.0 degrees celsius

Storage Tempurature Range:

-65.0/+150.0 degrees celsius

Features Provided:

Bipolar and programmed

Inclosure Material:

Ceramic

Inclosure Configuration:

Leadless flat pack

Output Logic Form:

Bipolar metal-oxide semiconductor

Input Circuit Pattern:

20 input

Case Outline Source And Designator:

C-4 mil-m-38510

Current Rating Per Characteristic:

100.00 milliamperes reverse current, dc

Terminal Surface Treatment:

Solder

Product Name:

Microcircuit, programmed pal

Voltage Rating And Type Per Characteristic:

-0.5 volts total supply and 7.0 volts total supply

Memory Device Type:

Pal

Hybrid Technology Type:

Monolithic

Test Data Document:

81349-mil-m-38510 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.). And 96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).

Terminal Type And Quantity:

28 printed circuit

Specification Data:

67268-5962-87671013a government standard

Purchase Description Identification:

04939-79931055-001

Departure From Cited Designator:

Altered by programming & marking

Shelf Life:

. . .

NSN 5962-01-372-9625

Memory Microcircuit - Page 2 of 2



			ure:	

--

Demilitarization:

Yes - demil/mli

Fiig:

A458a0